



Switch mode Power Rectifier.

employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

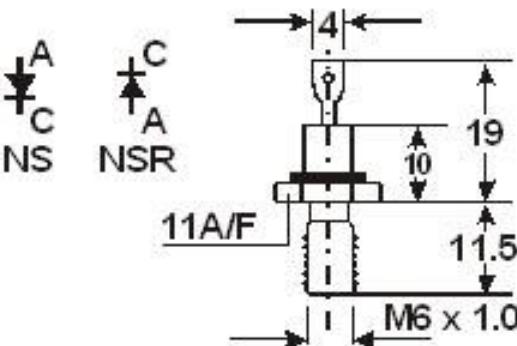
- Extremely Low V_{SD}
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- High Surge Capacity

Mechanical Characteristics :

- Case Welded steel, hermetically sealed
- Finish : All External Surfaces Corrosion Resistant and Terminal Lead is Readily Solderable

Solder Heat : The excellent heat transfer property of the heavy duty copper anode terminal which transmits heat away from the die requires that caution be used when attaching wires.

- Stud Torque: 15 lb-in max

30 AMPERE
45 VOLTS

MAXIMUM RATINGS

Ratings	Symbol	SD41	UNIT
Peak Repetitive Reverse Voltage	V _{RRM}	45	Volts
Working Peak Reverse Voltage	V _{WRM}		
PC Blocking Voltage	V _R		
Nonrepetitive Peak Reverse Voltage	V _{ROM}	54	Volts
Average Rectified Forward Current V _{Fwd(av)} ≤ 0.2 V _{Fwd} , T _c =85°C	I _o	30	Amps
Ambient Temperature Rated V _{RRM} , P _{FWAV} =0, R _{JA} =3.5°C/W	T _A	90	°C
Nonrepetitive Peak Surge Current (surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I _{ROM}	600 for one cycle	Amps
Operating and Storage Junction Temperature Range (Reverse voltage applied)	T _J , T _{SS}	-65 TO +150	°C
Peak Operating Junction Temperature (Forward Current Applied)	T _{J(pk)}	150	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction to case	R _{JD}	2.0	°C/W

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Maximum Instantaneous Forward Voltage (I _o =30 Amps) (I _o =60Amps) (I _o =60 Amps@150°C)	V _F	0.58 0.75 0.70	Volts
Maximum Instantaneous Reverse Current @ 25°C @125°C		50 125	ma ma